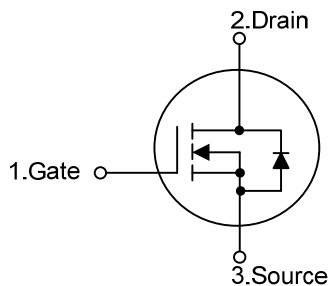


**15NM65-U2****Power MOSFET****15A, 650V N-CHANNEL
SUPER-JUNCTION MOSFET****DESCRIPTION**

The UTC 15NM65-U2 is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

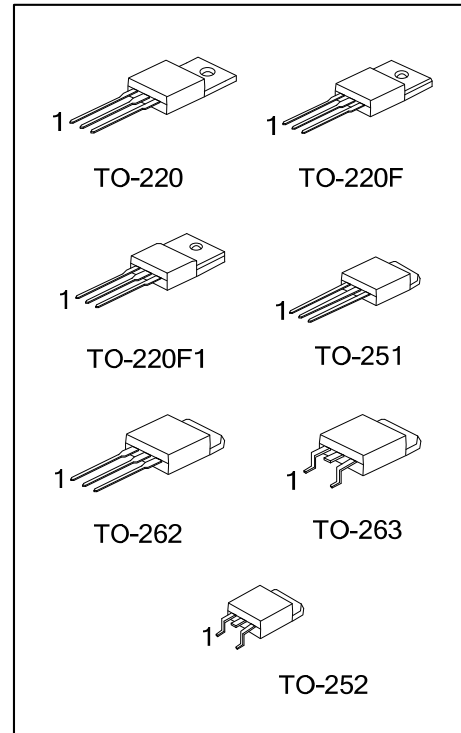
- * $R_{DS(ON)} \leq 0.43\Omega$ @ $V_{GS}=10V$, $I_D=7.5A$
- * By using Super Junction Structure
- * Fast Switching
- * With 100% Avalanche Tested

SYMBOL**ORDERING INFORMATION**

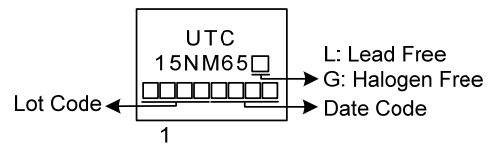
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15NM65L-TA3-T	15NM65G-TA3-T	TO-220	G	D	S	Tube
15NM65L-TF3-T	15NM65G-TF3-T	TO-220F	G	D	S	Tube
15NM65L-TF1-T	15NM65G-TF1-T	TO-220F1	G	D	S	Tube
15NM65L-TM3-T	15NM65G-TM3-T	TO-251	G	D	S	Tube
15NM65L-TN3-R	15NM65G-TN3-R	TO-252	G	D	S	Tape Reel
15NM65L-T2Q-T	15NM65G-T2Q-T	TO-262	G	D	S	Tube
15NM65L-TQ2-T	15NM65G-TQ2-T	TO-263	G	D	S	Tube
15NM65L-TQ2-R	15NM65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

15NM65G-TA3-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F TM3: TO-251, TN3: TO-252, T2Q: TO-262 TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current	Continuous	I_D	15	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	60	A
Avalanche Current (Note 3)		I_{AR}	3.1	A
Avalanche energy	Single Pulsed (Note 3)	E_{AS}	490	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	7.5	V/nS
Power Dissipation	TO-220/TO-262	P_D	168	W
	TO-263			
	TO-220F/TO-220F1		52	W
	TO-251/TO-252		75	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=102\text{mH}$, $I_{AS}=3.1\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J = 25^{\circ}\text{C}$.

4. $I_{SD} \leq 15\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J = 25^{\circ}\text{C}$.

■ **THERMAL CHARACTERISTICS**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
	TO-220F1/TO-262			
	TO-263			
	TO-251/TO-252		110	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-220/TO-262	θ_{JC}	0.74	$^{\circ}\text{C}/\text{W}$
	TO-263			
	TO-220F/TO-220F1		2.4	$^{\circ}\text{C}/\text{W}$
	TO-251/TO-252		1.67	$^{\circ}\text{C}/\text{W}$

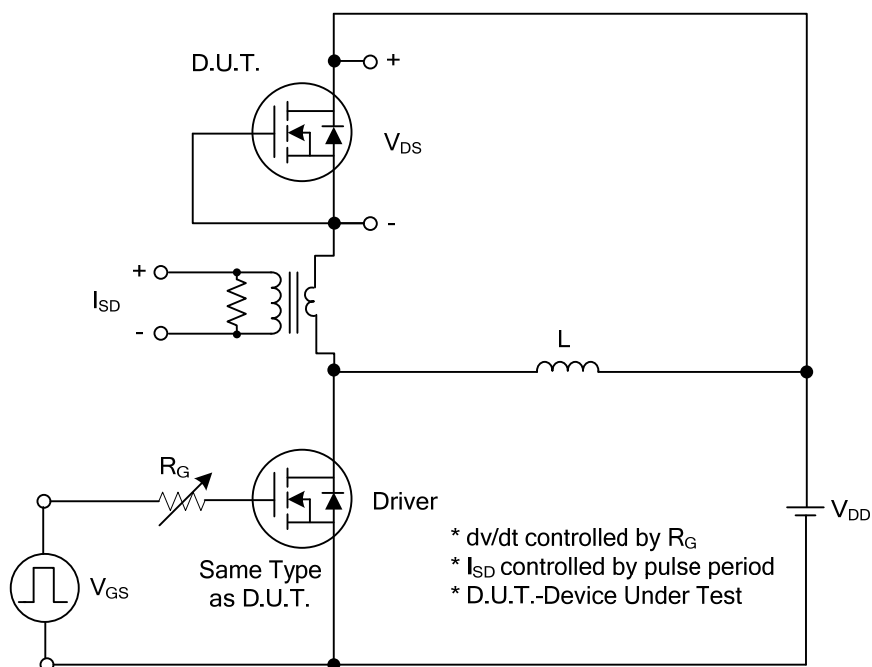
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{DS} =0V ,V _{GS} =+30V			+100	nA
	Reverse		V _{DS} =0V ,V _{GS} =-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D =250μA	2.5		4.5	V
Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =7.5A			0.43	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		894		pF
Output Capacitance		C _{OSS}			535		pF
Reverse Transfer Capacitance		C _{RSS}			25.5		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A , I _G =100μA (Note 1, 2)		95		nC
Gate to Source Charge		Q _{GS}			7.3		nC
Gate to Drain Charge		Q _{GD}			28		nC
Turn-on Delay Time (Note 1)		t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		64		ns
Rise Time		t _R			125		ns
Turn-off Delay Time		t _{D(OFF)}			238		ns
Fall-Time		t _F			134		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Pulsed Current		I _S				15	A
Drain-Source Diode Forward Voltage (Note 1)		I _{SM}				60	A
Maximum Body-Diode Continuous Current		V _{SD}	I _S =15A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =15A, V _{GS} =0V,		385		ns
Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		5.79		μC

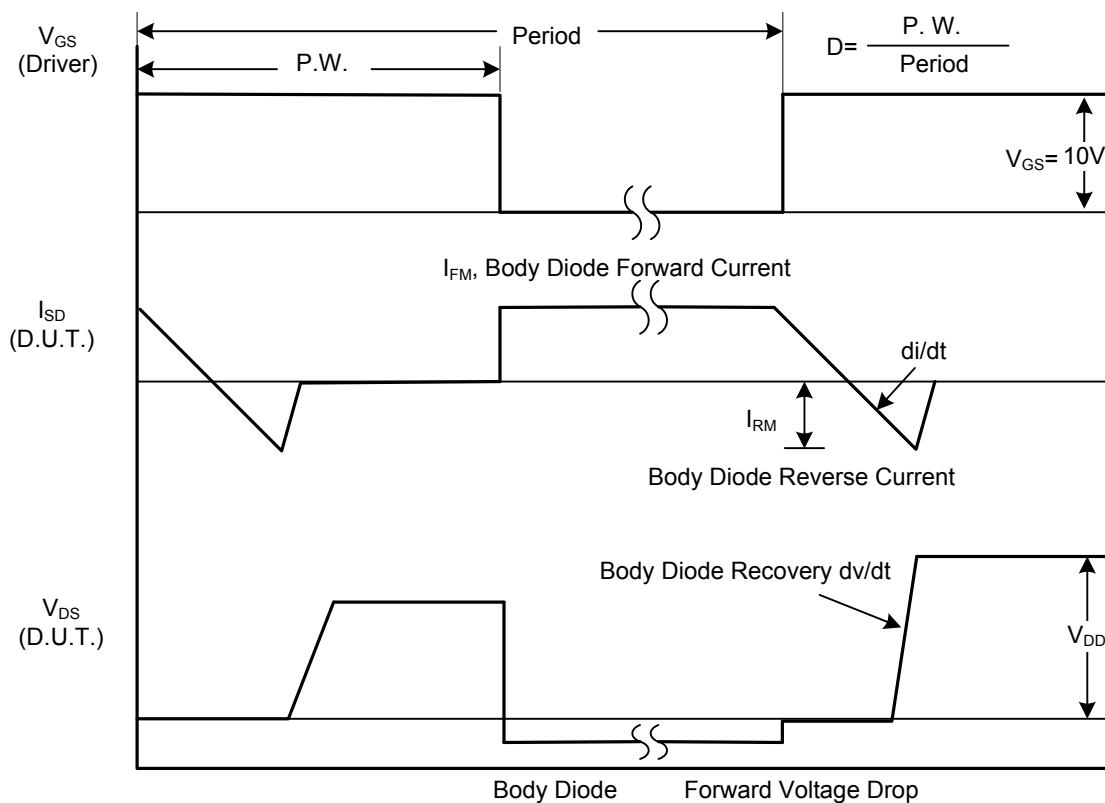
Note: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

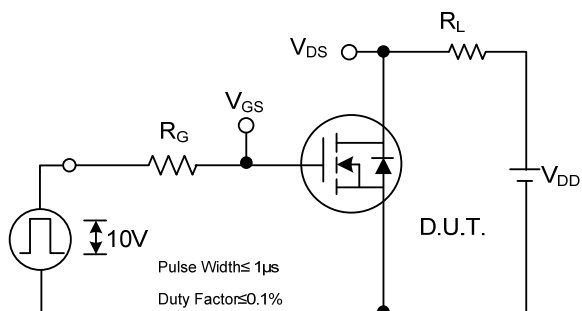


Peak Diode Recovery dv/dt Test Circuit

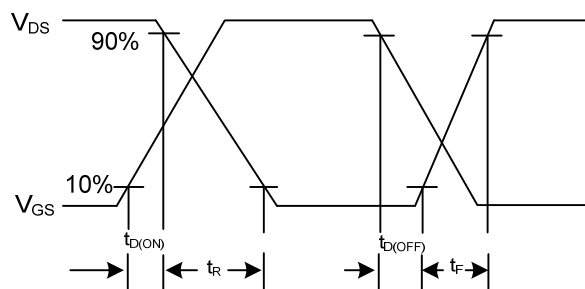


Peak Diode Recovery dv/dt Waveforms

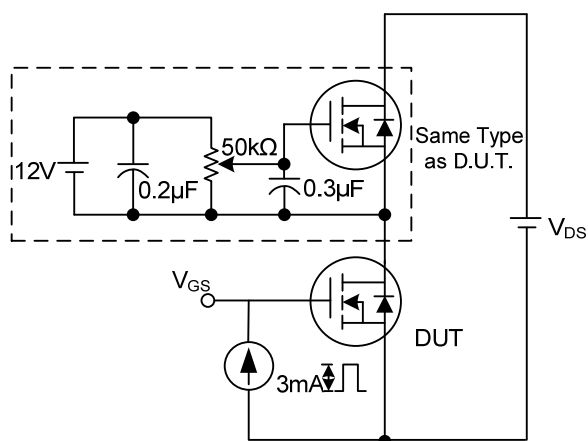
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



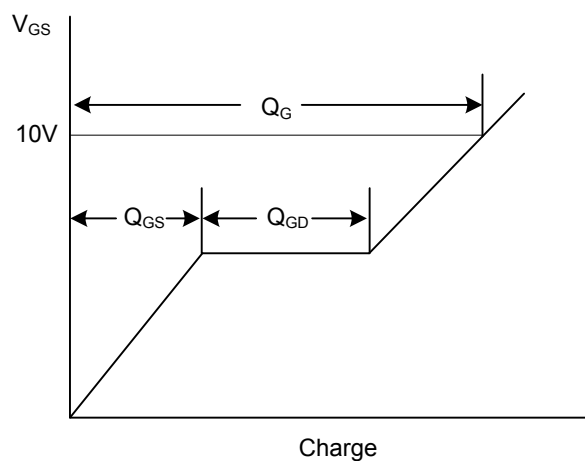
Switching Test Circuit



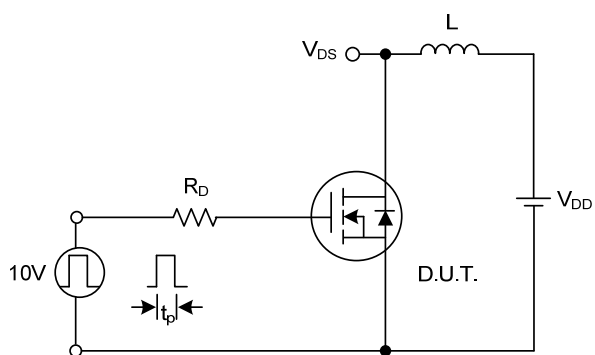
Switching Waveforms



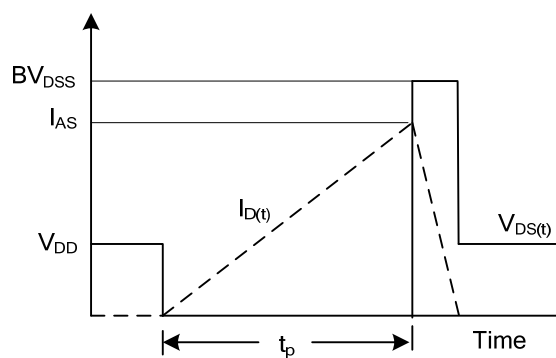
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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